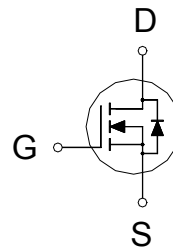


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
40V	12m Ω	32A

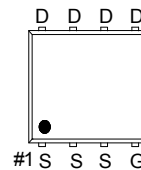


Features

- Pb-Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.



G. GATE
D. DRAIN
S. SOURCE

100% UIS Tested
100% Rg Tested

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ⁴	$T_C = 25\text{ }^\circ\text{C}$	I_D	32	A
	$T_C = 100\text{ }^\circ\text{C}$		20	
Pulsed Drain Current ¹		I_{DM}	51	
Continuous Drain Current ⁴	$T_A = 25\text{ }^\circ\text{C}$	I_D	11	
	$T_A = 70\text{ }^\circ\text{C}$		9	
Avalanche Current		I_{AS}	21	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	22	mJ
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	26.5	W
	$T_C = 100\text{ }^\circ\text{C}$		10.6	
Power Dissipation ³	$T_A = 25\text{ }^\circ\text{C}$	P_D	3.1	W
	$T_A = 70\text{ }^\circ\text{C}$		2	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10s$	$R_{\theta JA}$		40	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		61	
Junction-to-Case	Steady-State	$R_{\theta JC}$		4.7	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.

³The Power dissipation is based on $R_{\theta JA} t \leq 10s$ value.

⁴Package limitation current is 20A.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ C$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.75	2.3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 32V, V_{GS} = 0V$			1	μA
		$V_{DS} = 30V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 11A$		9.5	16	m Ω
		$V_{GS} = 10V, I_D = 11A$		8.2	12	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 11A$		80		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 20V, f = 1MHz$		962		pF
Output Capacitance	C_{oss}			111		
Reverse Transfer Capacitance	C_{rss}			69		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		1.8		Ω
Total Gate Charge ²	Q_g	$V_{GS} = 10V$	$V_{DS} = 20V, V_{GS} = 10V, I_D = 11A$		18	nC
		$V_{GS} = 4.5V$			9.6	
Gate-Source Charge ²	Q_{gs}			2.4		
Gate-Drain Charge ²	Q_{gd}			4.5		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 20V, I_D \cong 11A, V_{GS} = 10V, R_{GEN} = 6\Omega$			20	
Rise Time ²	t_r			12		
Turn-Off Delay Time ²	$t_{d(off)}$			31		
Fall Time ²	t_f			13		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)

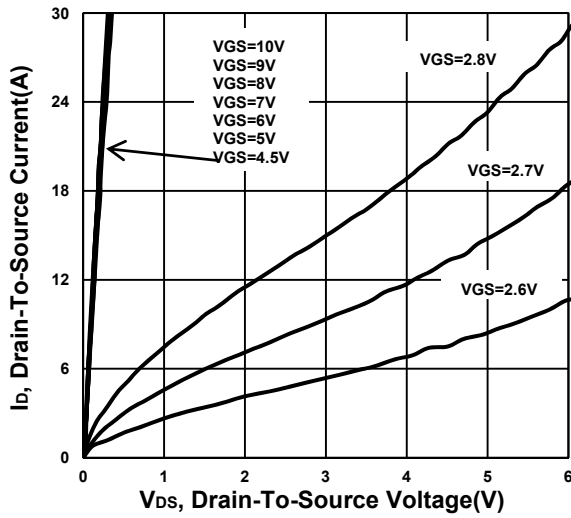
Continuous Current ³	I _S			20	A
Forward Voltage ¹	V _{SD}	I _F = 11A, V _{GS} = 0V		1.3	V
Reverse Recovery Time	t _{rr}	I _F = 11A, dI _F /dt = 100A / μS		9.5	nS
Reverse Recovery Charge	Q _{rr}			2	nC

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

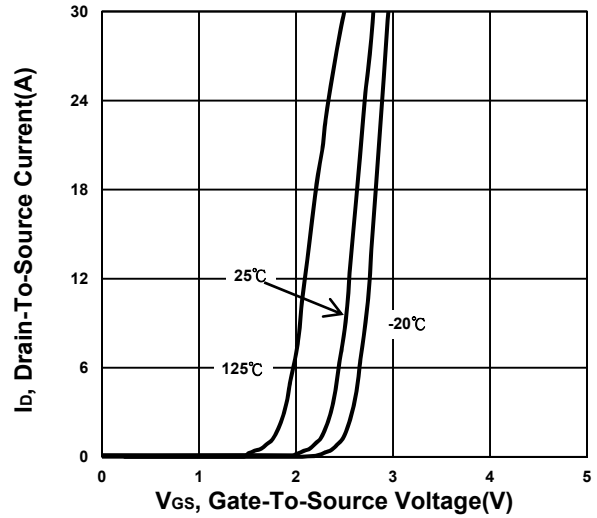
²Independent of operating temperature.

³Package limitation current is 20A.

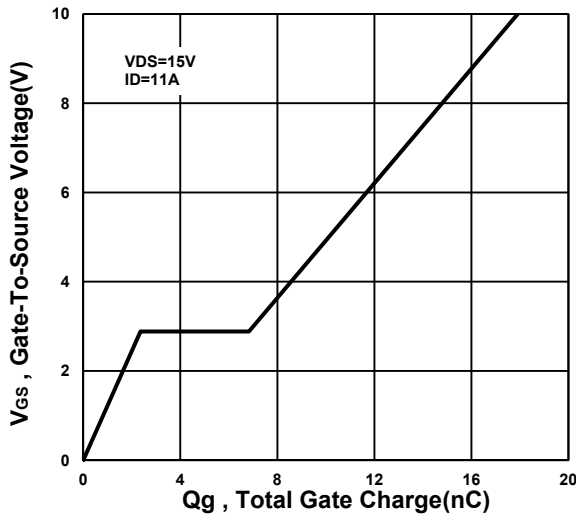
Output Characteristics



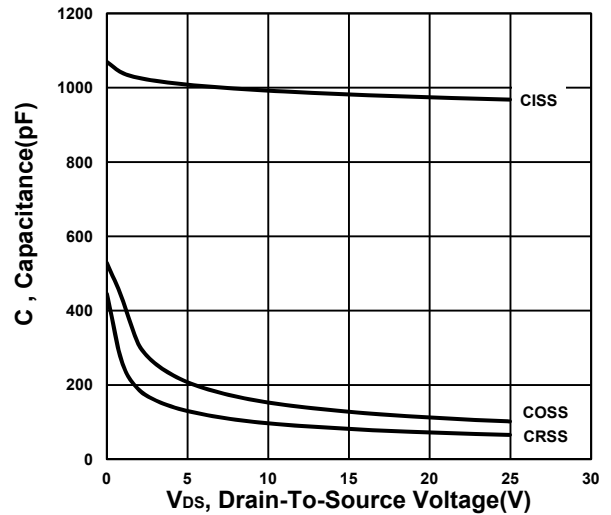
Transfer Characteristics



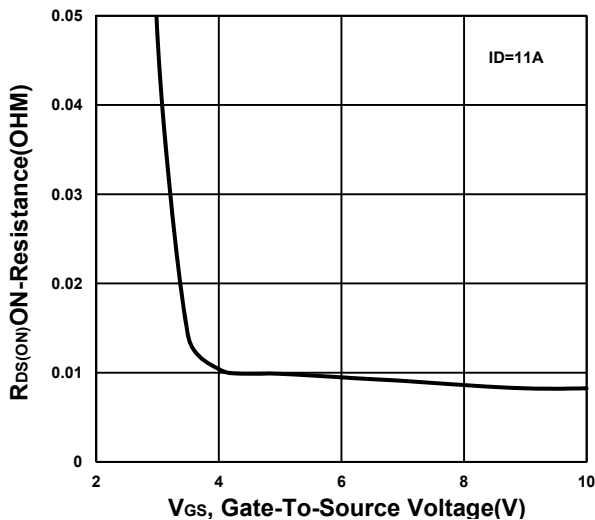
Gate charge Characteristics



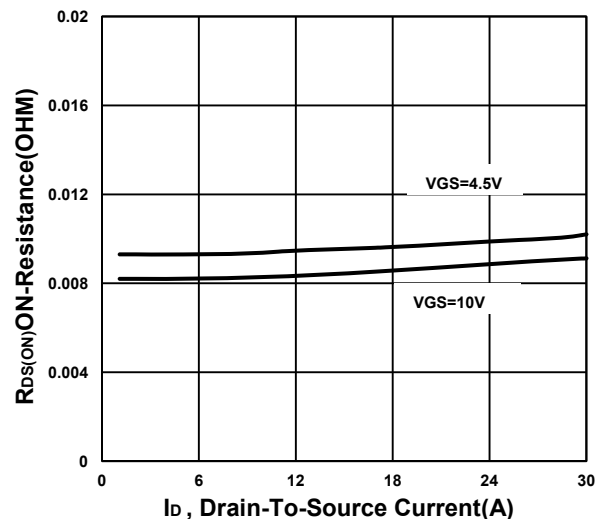
Capacitance Characteristic



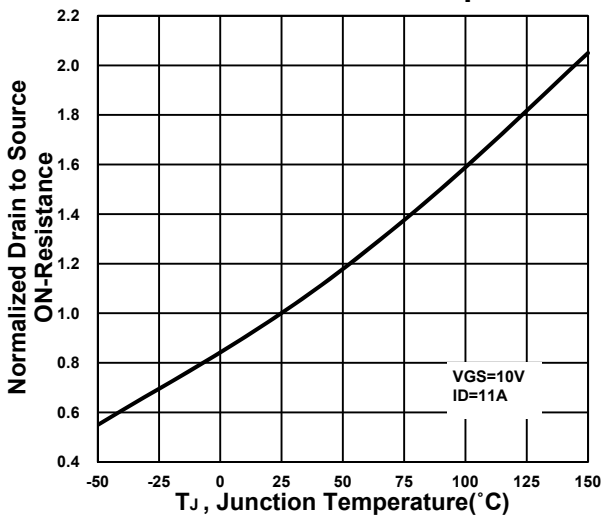
On-Resistance VS Gate-To-Source



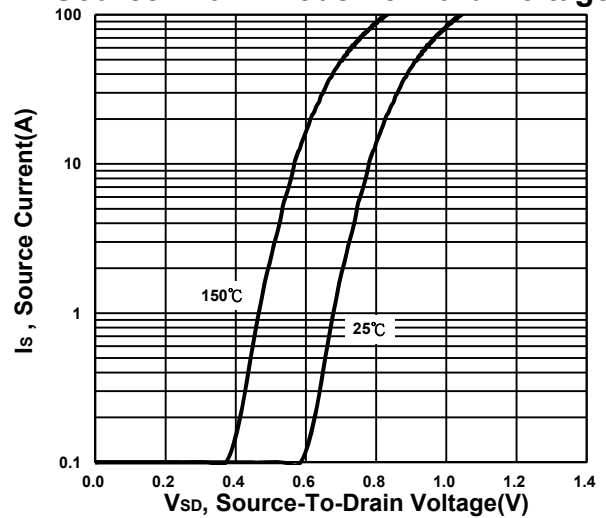
On-Resistance VS Drain Current



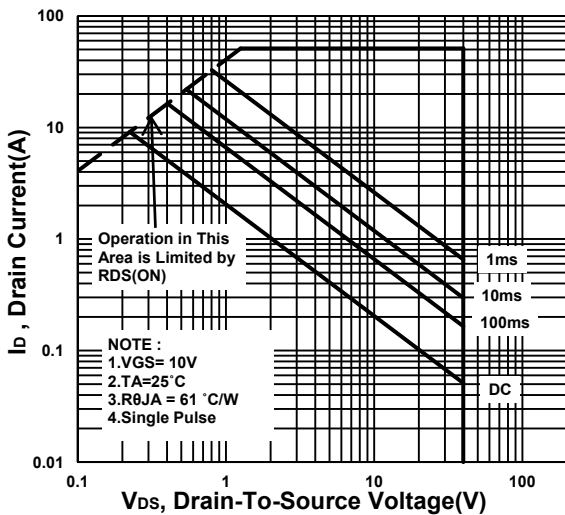
On-Resistance VS Temperature



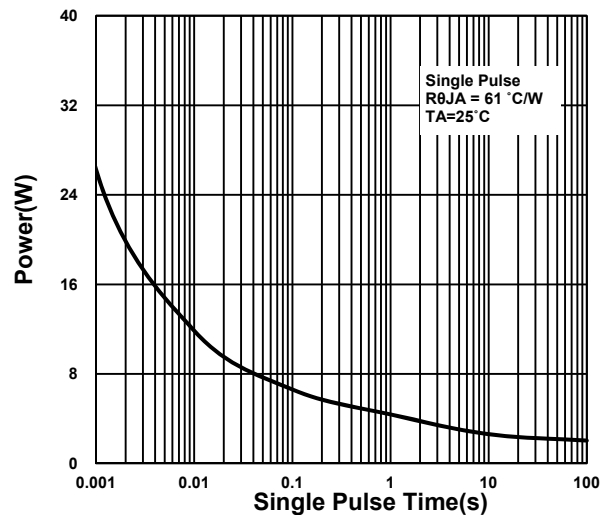
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

